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a second diffusion region formed in the substrate adjacent to and spaced from the first diffusion region;  
at least one contact for making a conductive connection to the first diffusion region;  
a channel formed in a third region between the first and second diffusion regions;  
and  
a plurality of current divider segments unevenly and randomly distributed within the first diffusion region.

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92. (Amended) An electrostatic discharge protection device, comprising:  
a substrate;  
a first diffusion region formed in the substrate;  
a second diffusion region formed in the substrate adjacent to and spaced from the first diffusion region;  
contacts for making a conductive connection to the first diffusion region;  
a channel formed in a third region between the first and second diffusion regions;  
and  
a plurality of current divider segments formed within the first diffusion region and being unevenly and randomly distributed therein.

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100. (Amended) The device of claim 99, wherein said segments include the first segment formed of a polysilicon layer or a field oxide layer; and the second segment formed of a polysilicon layer or a field oxide layer.

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